

SOJ HIGH-FREQUENCY CRYSTAL OSCILLATOR

SG-615 series

- High-density mounting-type SMD.
- A general-purpose SMD with heat-resisting cylindrical AT-cut crystal unit and allowing almost the same soldering temperature as SMD IC.
- Cylindrical AT crystal unit builtin, thus assuring high reliability.
- Provided with output enable function.
- Low current consumption.

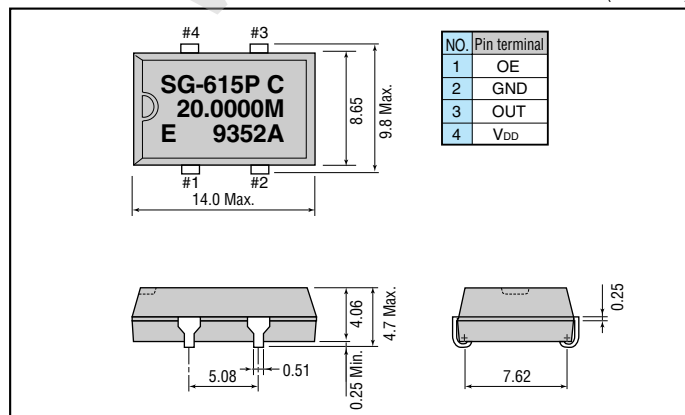
Specifications (characteristics)

Item		Symbol	SG-615P	SG-615PTJ	SG-615PH	Remarks
			Specifications			
Output frequency range		f ₀	1.0250 MHz to 26.0000 MHz	26.0001 MHz to 66.6667 MHz		
Power source voltage	Max. supply voltage	V _{DD} -GND		-0.3 V to +7.0 V		
	Operating voltage	V _{DD}		5.0 V±0.5 V		
Temperature range	Storage temperature	T _{STG}	-55 °C to +125 °C			Stored as bare product after unpacking 55 MHz Max.(-40 °C to +85 °C)
	Operating temperature	T _{OPR}	-20 °C to 70 °C (-40 °C to 85 °C)			
Soldering condition		T _{SOL}	Twice at under 260 °C within 10 s or under 230 °C within 3 min.			
Frequency stability		Δf/f ₀	B: ±50 x 10 ⁻⁶ C: ±100 x 10 ⁻⁶			B type is possible up to 55 MHz
Current consumption		I _{OP}	23 mA Max.	35 mA Max.		No load condition
Duty	C-MOS level	t _w /t	40 % to 60 %	—	40 % to 60 %	C-MOS load: 1/2V _{DD}
	TTL level		45 % to 55 %		—	TTL load: 1.4 V
Output voltage		V _{OH}	V _{DD} -0.4 V Min.	2.4 V Min.	V _{DD} -0.4 V Min.	
		(I _{OH})	-400 μA		-4 mA	
		V _{OL}	0.4 V Max.			
		(I _{OL})	16 mA	8 mA	4 mA	
Output load condition (fan out)	C-MOS	C _L	50 pF Max.	—	50 pF Max.	C _L ≤15 pF
	TTL	N	10 TTL Max.	5 TTL Max.	—	
Output enable/disable input voltage		V _{IH}	2.0 V Min.	3.5 V Min.	2.0 V Min.	I _{IH} =1 μA Max.(OE=V _{DD})
		V _{IL}	0.8 V Max.	1.5 V Max.	0.8 V Max.	I _{IL} =100 μA Min.(OE=GND) I _{IL} =500 μA Min.(OE=GND) PTJ
Output disable current		I _{OE}	12 mA Max.	28 mA Max.	20 mA Max.	OE=GND
Output rise time	C-MOS level	t _{TLH}	8 ns Max.	—	7 ns Max.	C-MOS load: 20 %→80 % V _{DD}
	TTL level			5 ns Max.	—	TTL load: 0.4 V→2.4 V
Output fall time	C-MOS level	t _{THL}	8 ns Max.	—	7 ns Max.	C-MOS load: 80 %→20 % V _{DD}
	TTL level			5 ns Max.	—	TTL load: 2.4 V→0.4 V
Oscillation start up time		t _{OSC}	4 ms Max.	10 ms Max.		Time at 4.5 V to be 0 s
Aging		f _a		±5 x 10 ⁻⁹ /year Max.		T _a = +25 °C, V _{DD} = 5 V, first year
Shock resistance		S.R.		±20 x 10 ⁻⁶ Max.		Three drops on a hard board from 750 mm or excitation test with 29400 m/s ² x 0.3 ms x 1/2sine wave in 3 directions

Note: • Unless otherwise stated, characteristics (specifications) shown in the above table are based on the rated operating temperature and voltage condition.
• External by-pass capacitor is recommended.

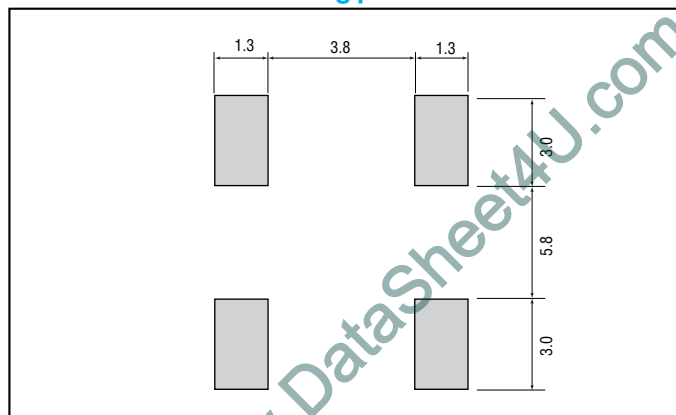
External dimensions

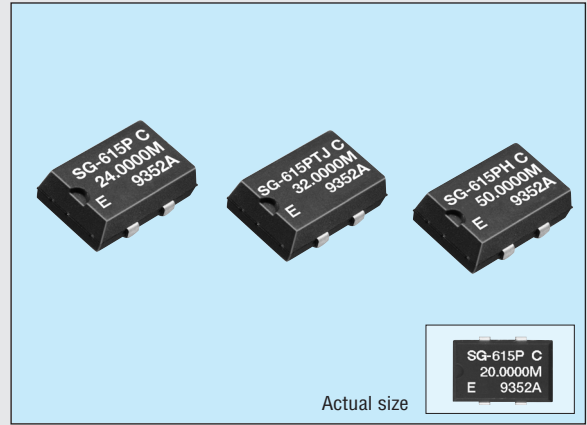
(Unit: mm)



Recommended soldering pattern

(Unit: mm)





Specifications (characteristics)

Item		Symbol	SG-615PTW/STW	SG-615PHW/SHW	SG-615PCW/SCW	Remarks
			Specifications			
Output frequency range		f_0	55.0001 MHz to 135.0000 MHz		26.0001 MHz to 135.0000 MHz	
Power source voltage	Max. supply voltage	V_{DD-GND}	-0.5 V to +7.0 V			
	Operating voltage	V_{DD}	5.0 V $\pm$ 0.5 V		3.3 V $\pm$ 0.3 V	
Temperature range	Storage temperature	T_{STG}	-55 °C to +125 °C			
	Operating temperature	T_{OPR}	-20 °C to +70 °C		-40 °C to +85 °C	
Soldering condition (lead part)		T_{SOL}	Twice at under 260 °C within 10 s or under 230 °C within 3 min.			
Frequency stability		$\Delta f/f_0$	B: $\pm 50 \times 10^{-6}$ C: $\pm 100 \times 10^{-6}$			-20 °C to +70 °C
			M: $\pm 100 \times 10^{-6}$			40 °C to +85 °C
Current consumption		I_{OP}	45 mA Max.		28 mA Max.	No load condition
Output disable current		I_{OE}	30 mA Max.		16 mA Max.	OE=GND
Output disable current		I_{ST}	50 μ A Max.			ST=GND
Duty	C-MOS level	tw/t	—		40 % to 60 %	C-MOS load: 1/2 V_{DD}
	TTL level		40 % to 60 %		—	TTL load: 1.4 V
Output voltage		V_{OH}	V_{DD} -0.4 V Min.			I_{OH} = -16 mA (*TW/HW)/-8 mA (*CW)
		V_{OL}	0.4 V Max.			I_{OL} = -16 mA (*TW/HW)/8 mA (*CW)
Output load condition (fan out)		C_L	15 pF Max.			
Output enable/disable input voltage		V_{IH}	2.0 V Min.		0.7 V_{DD} Min.	OE,ST
		V_{IL}	0.8 V Max.		0.2 V_{DD} Min.	OE,ST
Output rise time	C-MOS level	t_{RLH}	—		4 ns Max.	C-MOS load: 20 % $\rightarrow$ 80 % V_{DD}
	TTL level		4 ns Max.		—	TTL load: 0.4 V $\rightarrow$ 2.4 V
Output fall time	C-MOS level	t_{FHL}	—		4 ns Max.	C-MOS load: 80 % $\rightarrow$ 20 % V_{DD}
	TTL level		4 ns Max.		—	TTL load: 2.4 V $\rightarrow$ 0.4 V
Oscillation start up time		t_{OSC}	10 ms Max.			Time at 4.5 V to be 0 s
Aging		f_a	$\pm 5 \times 10^{-6}$ /year Max.			T_a =+25 °C, V_{DD} =5 V
Shock resistance		S.R.	$\pm 20 \times 10^{-6}$ Max.			Three drops on a hard board from 750 mm or excitation test with 29400 m/s ² x 0.3 ms x 1/2 sine wave in 3 directions

Operating condition and Frequency band

Operating condition		1 MHz	50 MHz	100 MHz	150 MHz
5 V $\pm$ 0.5 V	Frequency stability:B (-20 to +70 °C)	1.025	26	55	135
		SG-615P	SG-615PTJ/PH	SG-615PTW/STW/PHW/SHW	
	Frequency stability:C (-20 to +70 °C)	1.025	26	66.667	135
		SG-615P	SG-615PTJ/PH	SG-615PTW/STW/PHW/SHW	
3.3 V $\pm$ 0.3 V	Frequency stability:B (-20 to +70 °C)		26		135
			SG-615PCW/SCW		
	Frequency stability:C (-20 to +70 °C)		26		135
			SG-615PCW/SCW		
	Frequency stability:M (-40 to +85 °C)		26		135
			SG-615PCW/SCW		